

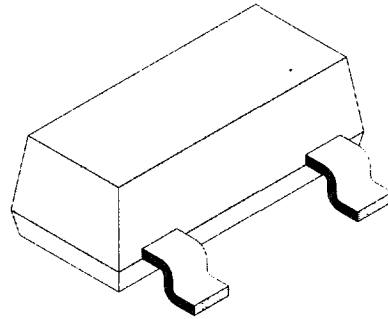
## Silicon NPN Phototransistor

### Description

TEMT2100 is a high speed silicon NPN epitaxial planar phototransistor in miniature SOT-23 package for surface mounting on printed boards. Due to its waterclear epoxy the device is sensitive to visible and near infrared radiation.

### Features

- Standard SOT-23 clear plastic package
- Extra wide viewing angle  $\phi = \pm 70^\circ$
- Especially for surface mounting on printed board
- Small mechanical tolerances
- Fast response times
- Suitable for visible and near infrared radiation



94 8550

### Applications

Detector in electronic control and drive circuits in SMD technique

### Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Collector Emitter Voltage		$V_{CEO}$	70	V
Emitter Collector Voltage		$V_{ECO}$	5	V
Collector Current		$I_C$	50	mA
Peak Collector Current	$t_p/T = 0.5, t_p \leq 10 \text{ ms}$	$I_{CM}$	100	mA
Total Power Dissipation	$T_{amb} \leq 25^\circ\text{C}$	$P_{tot}$	75	mW
Junction Temperature		$T_j$	100	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55...+100	$^\circ\text{C}$
Soldering Temperature	$t \leq 5 \text{ s}$	$T_{sd}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{thJA}$	1000	K/W

**Basic Characteristics**

$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	$I_C = 1\text{ mA}$	$V_{(BR)CEO}$	70			V
Collector Dark Current	$V_{CE} = 20\text{ V}, E = 0$	$I_{CEO}$		1	200	nA
Collector Emitter Capacitance	$V_{CE} = 5\text{ V}, f = 1\text{ MHz}, E=0$	$C_{CEO}$		3		pF
Collector Light Current	$E_c=1\text{ mW/cm}^2, \lambda=950\text{ nm}, V_{CE}=5\text{ V}$	$I_{ca}$	0.30	0.45		mA
Angle of Half Sensitivity		$\phi$		$\pm 70$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		850		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		620...980		nm
Collector Emitter Saturation Voltage	$E_c=1\text{ mW/cm}^2, \lambda=950\text{ nm}, I_C=0.1\text{ mA}$	$V_{CEsat}$			0.3	V
Turn-On Time	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$t_{on}$		2.0		$\mu\text{s}$
Turn-Off Time	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$t_{off}$		2.3		$\mu\text{s}$
Cut-Off Frequency	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$f_c$		180		kHz

**Typical Characteristics** ( $T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified)

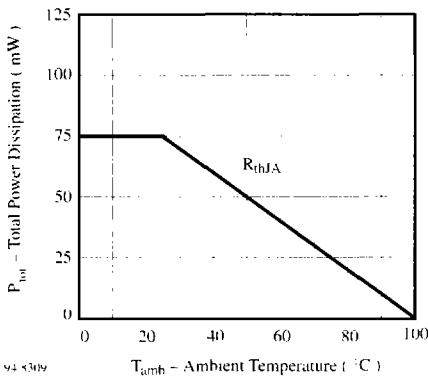


Figure 1. Total Power Dissipation vs. Ambient Temperature

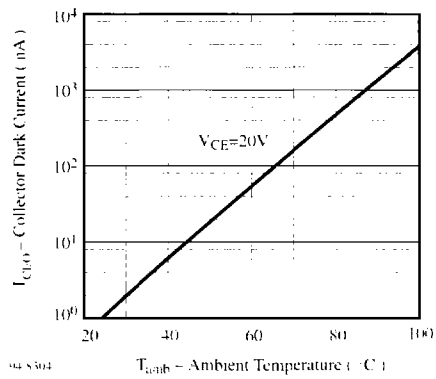


Figure 2. Collector Dark Current vs. Ambient Temperature

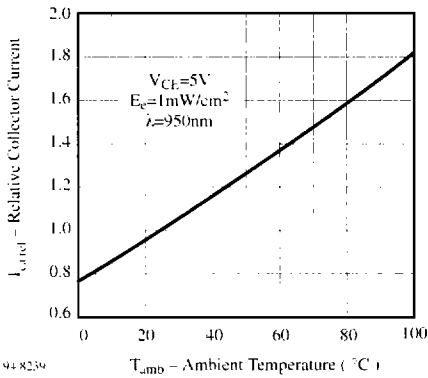


Figure 3. Relative Collector Current vs. Ambient Temperature

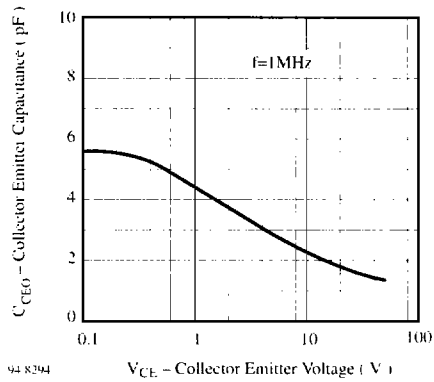


Figure 6. Collector Emitter Capacitance vs. Collector Emitter Voltage

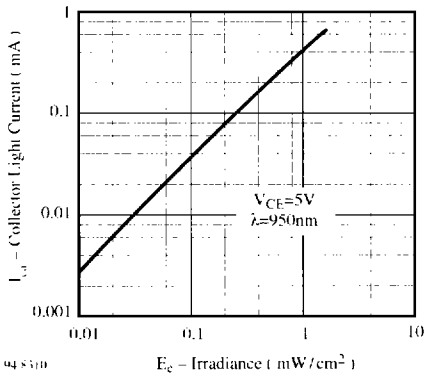


Figure 4. Collector Light Current vs. Irradiance

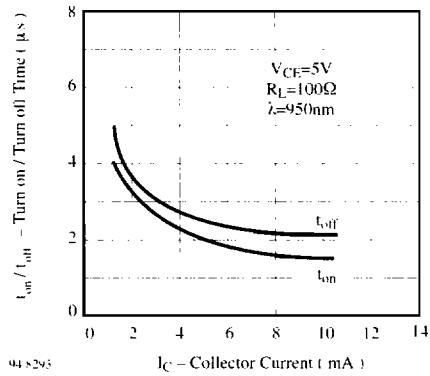


Figure 7. Turn On/Turn Off Time vs. Collector Current

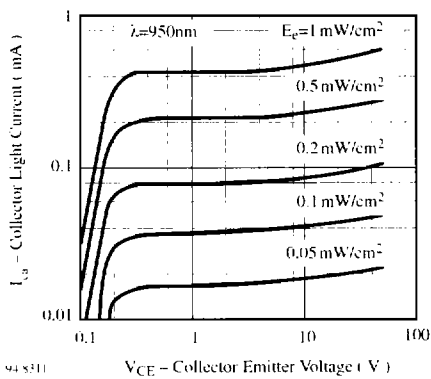


Figure 5. Collector Light Current vs. Collector Emitter Voltage

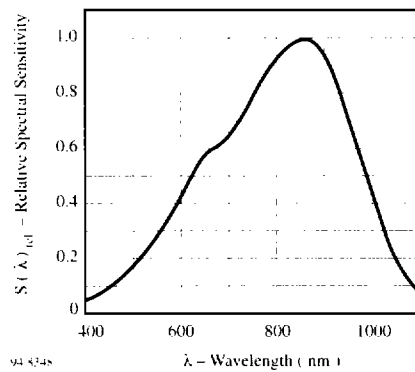


Figure 8. Relative Spectral Sensitivity vs. Wavelength

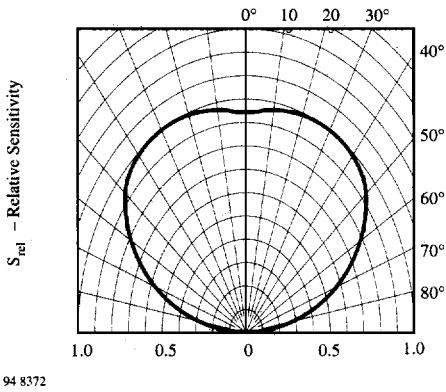
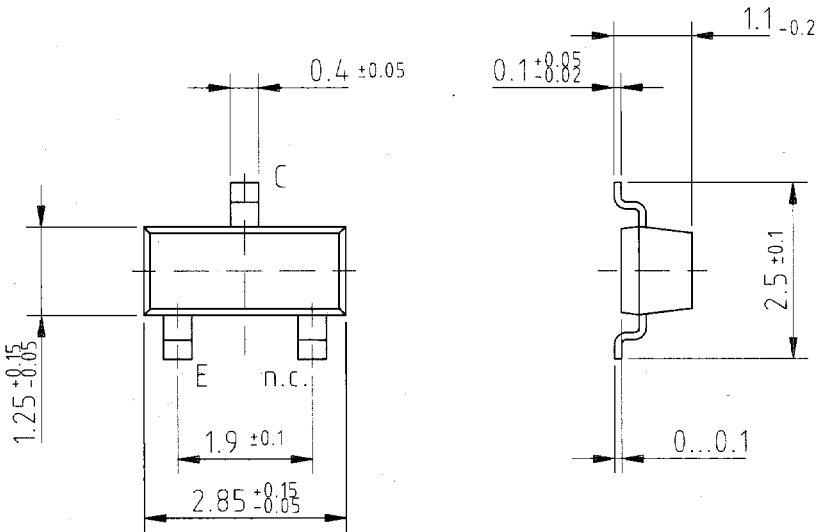


Figure 9. Relative Radiant Sensitivity vs. Angular Displacement

**Dimensions in mm**



95 11349

technical drawings  
according to DIN  
specifications